

# 2SA872A

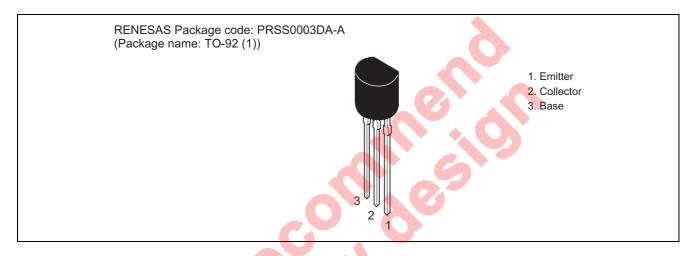
# Silicon PNP Epitaxial

REJ03G0631-0200 (Previous ADE-208-1001) Rev.2.00 Aug.10.2005

### **Application**

- Low frequency low noise amplifier
- Complementary pair with 2SC1775A

#### **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	-120	V
Collector to emitter voltage	V <sub>CEO</sub>	-120	V
Emitter to base voltage	$V_{EBO}$	<b>-</b> 5	V
Collector current	I <sub>C</sub>	-50	mA
Collector power dissipation	P <sub>C</sub>	300	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-50 to +150	°C

#### **Electrical Characteristics**

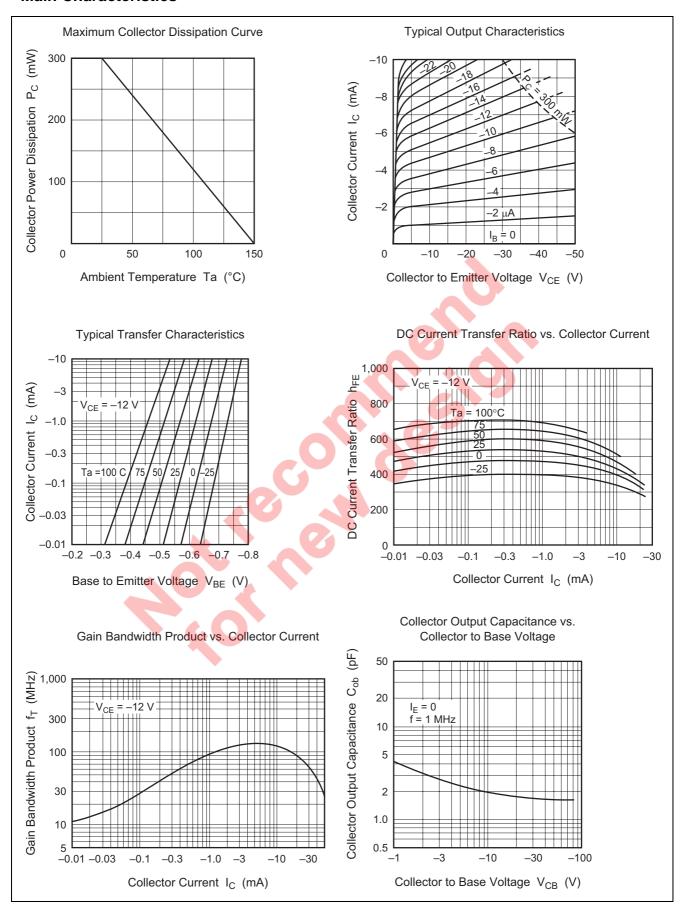
 $(Ta = 25^{\circ}C)$ 

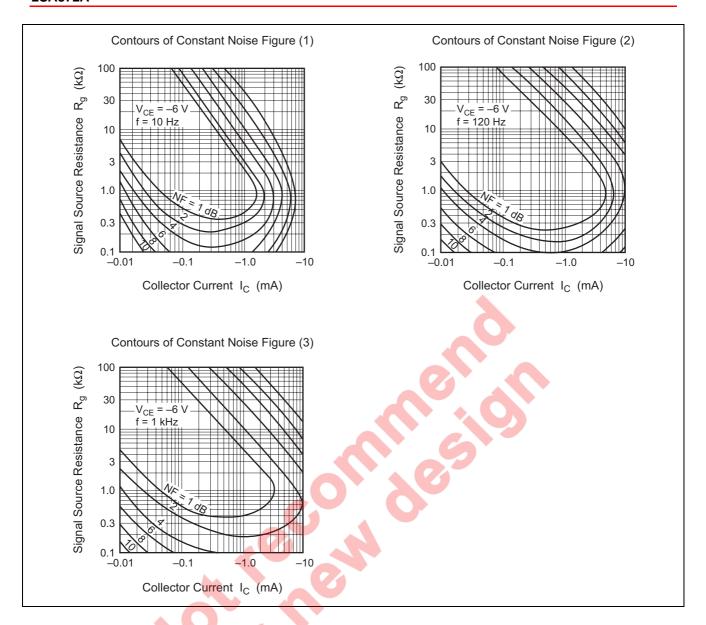
		Symbol	Min	Тур	Max	Unit	Test conditions
$ \begin{array}{ c c c c } \hline \text{Collector cutoff current} & I_{\text{CBO}} &$	Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	-120	_	_	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Collector cutoff current		_	_	_	μΑ	$V_{CB} = -75 \text{ V}, I_{E} = 0$
			_	_	-0.5	μΑ	$V_{CE} = -100 \text{ V}, I_{E} = 0$
	DC current transfer ratio	h <sub>FE1</sub> *1	250	_	800		$V_{CE} = -12 \text{ V},$
Base to emitter voltage $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$							$I_C = -2 \text{ mA}$
Base to emitter voltage $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		h <sub>FE2</sub>	160	_	_		
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$							$I_C = -0.1 \text{ mA}$
	Base to emitter voltage	$V_{BE}$	_	_	-0.75	V	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$							
	Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	_		-0.5	V	
Collector output capacitance $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$							
	Gain bandwidth product	f⊤	_	120	_	MHz	
Noise figure $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$					1		
Noise figure $ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Collector output capacitance	Cob	_	1.8	_	pF	
Note: 1. The 2SA872A is grouped by $h_{\text{FE1}}$ as follows.							
Note: 1. The 2SA872A is grouped by $h_{FE1}$ as follows.	Noise figure	NF	_	_	5.0	dB	
—   —   1.5   dB   f = 1 kHz							
Note: 1. The 2SA872A is grouped by h <sub>FE1</sub> as follows.    D					1 -		<u> </u>
D E 250 to 500 400 to 800			_		1.5	gB	f = 1 KHZ
					5	•	
				8			

Note: 1. The 2SA872A is grouped by  $h_{\text{FE1}}$  as follows.

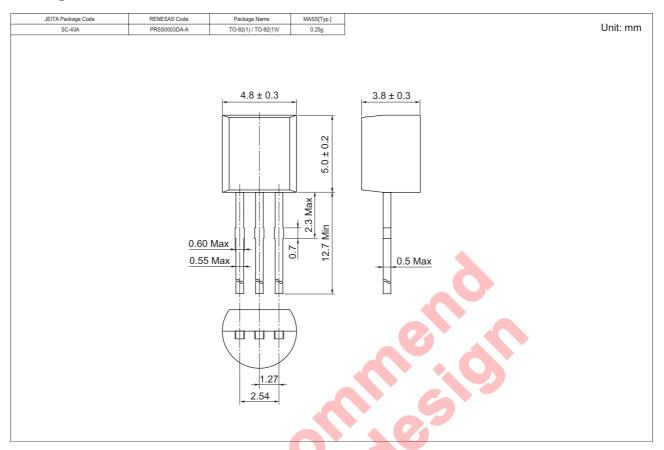
D	E
250 to 500	400 to 800

#### **Main Characteristics**





## **Package Dimensions**



## **Ordering Information**

Part Name	Quantity	Shipping Container
2SA872ADTZ	2500	Hold Box, Radial Taping
2SA872AETZ		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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